TOSHIBA Transistor Silicon PNP Triple Diffused Type (PCT process)

2SA1200

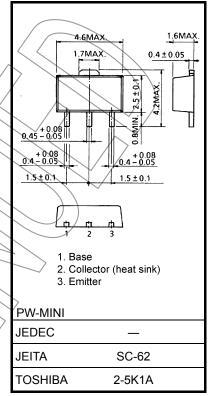
High Voltage Switching Applications

Unit: mm

- High voltage: VCEO = -150 V
- High transition frequency: $f_T = 120 \text{ MHz}$ (typ.)
- Small flat package
- Pc = 1 to 2 W (mounted on a ceramic substrate)
- Complementary to 2SC2880

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-150	X
Collector-emitter voltage	V _{CEO}	-150	V
Emitter-base voltage	V _{EBO}	/ 5	V
Collector current	Ic	-50	mA
Base current	ΙΒ		mA
	P _C	500	
Collector power dissipation	P _C (Note 1)	800	mW
Junction temperature	Ti.	150	°C
Storage temperature range	T _{stg}	-55 to 150	∕°C

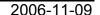


Weight: 0.05 g (typ.)

Note 1: 2SA1200 mounted on a ceramic substrate (250 mm² × 0.8 t)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.)

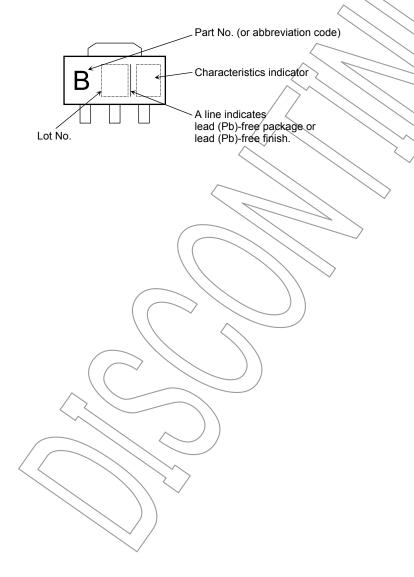


Electrical Characteristics (Ta = 25°C)

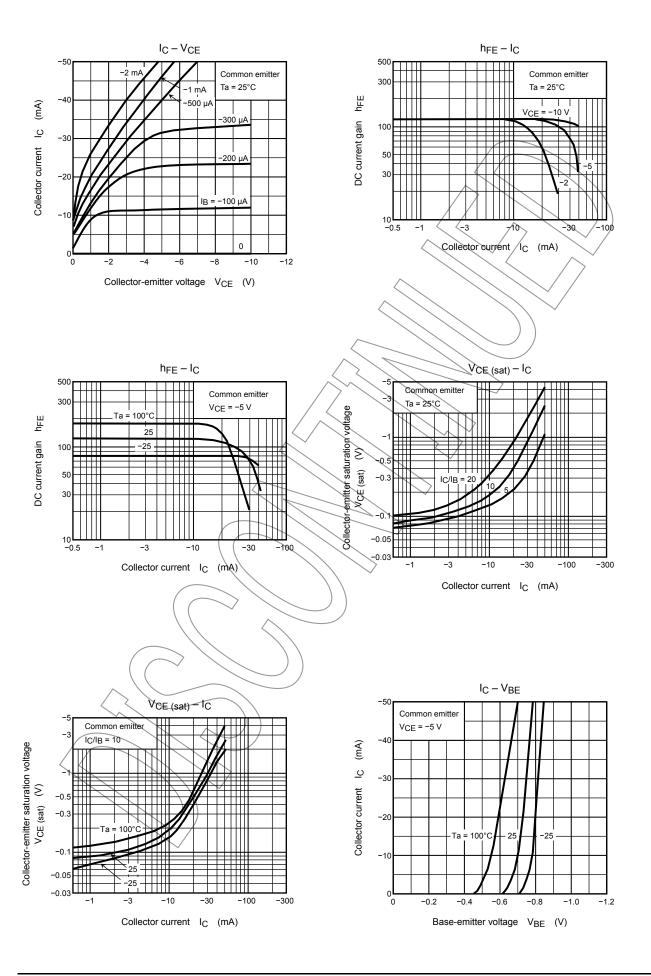
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = -150 V, I _E = 0	_	_	-0.1	μΑ
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$	_	_	-0.1	μA
DC current gain	h _{FE} (Note 3)	V _{CE} = -5 V, I _C = -10 mA	70	_	240	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = -10 mA, I _B = -1 mA		/_/	-0.8	V
Base-emitter voltage	V _{BE}	V _{CE} = -5 V, I _C = -30 mA	<u></u>	-/	-0.9	V
Transition frequency	f _T	V _{CE} = -30 V, I _C = -10 mA	7	120	/-/	MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	_	4.0	5.0	pF

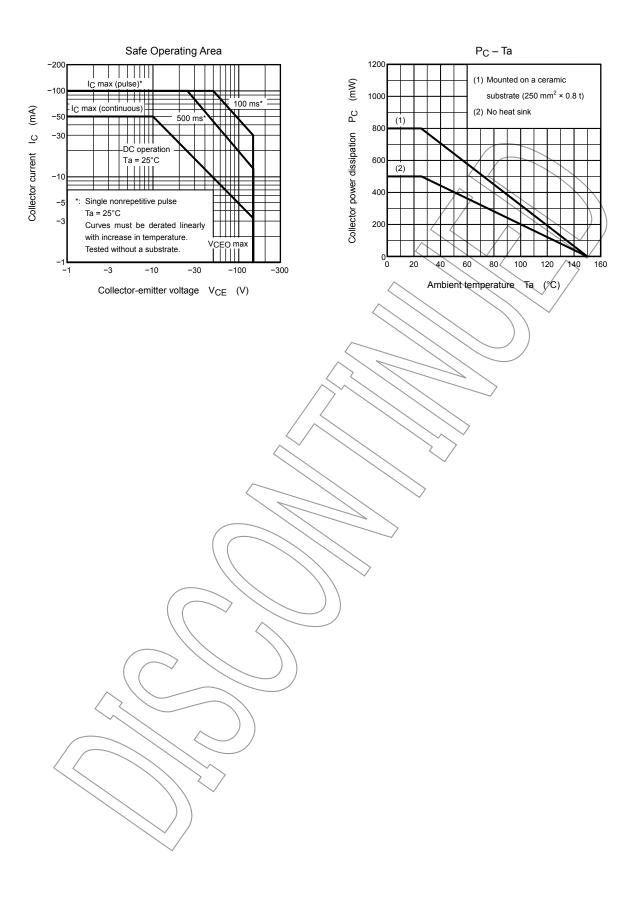
Note 3: h_{FE} classification O: 70 to 140, Y: 120 to 240

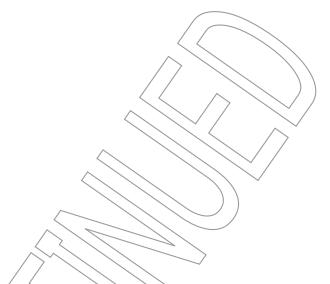




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